

Electrostatic Engineering of Nanotube Transistors for Improved Performance

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With decreasing device dimensions, the performance of carbon nanotube field-effect transistors (CNFETs) is limited by high I_{on} currents except at low drain voltages. We show that an asymmetric design improves the performance, reducing I_{on} currents and extending the usable range of drain voltage. The improvement is most dramatic for ambipolar Schottky-barrier CNFETs. Moreover, this approach allows a single device to exhibit equally good performance as an n- or p-type transistor, by changing only the sign of the drain voltage. Even for CNFETs having ohmic contacts, an asymmetric design can greatly improve the performance for small-bandgap nanotubes.

The performance of carbon nanotube field-effect transistors (CNFETs) can be greatly improved in many respects by scaling the devices to smaller size^{1,4}. However, the improvements with smaller size are accompanied by the undesired effect of a lowered I_{on}/I_{off} ratio at typical drain voltages. This restricts the range of usable drain voltage, which in turn limits the achievable I_{on} currents. Most CNFETs to date operate as Schottky barrier (SB) CNFETs^{1,7}, and the issue has been studied in detail for such devices^{7,8}. But the problem occurs even for ohmic contacts, especially for small-bandgap tubes, as shown below.

Here, we propose a novel device design for CNFETs that can be scaled down in size for good turn-on performance without severe restrictions on the usable drain voltage. The key idea of the new design is to have large electric fields at the source contact but small fields at the drain, to suppress unwanted tunneling. A related approach has recently been demonstrated for Si-based SB-FETs⁹.

For an ambipolar SB-CNFT, the asymmetric design can suppress either the p- or the n-type branch of the ambipolar transport characteristic, depending only on the sign of the drain voltage. Thus the same device can act as an excellent p- or n-type transistor, and the turn-on performance for both types is controlled by the electrostatics (the geometry of the contact and gate) at the source electrode. By choosing metals of different work function for the gates, it should be possible to fabricate complementary SB-CNFTs that have the desired alignment of transfer characteristics (I vs. V_g) for standard logic applications.

For a SB-CNFT, the asymmetric design solves the problem of I_{off} current that increases exponentially with drain voltage, so it allows larger I_{on} currents. This is a critical issue as the device dimensions decrease^{7,8}. Moreover, even for a CNFT having ohmic contacts¹⁰, e.g. to the valence band, suppressing the current into the conduction band can be essential when the nanotube (NT) bandgap is small.

Two examples of possible asymmetric device geometries are shown in Fig. 1. The first design, Fig. 1(a), relies on having a different thickness for the bottom oxide at the source and drain contacts. The second design,

Fig. 1(b), employs a top gate close to the source contact but not the drain. Other ways of engineering the electric fields are possible, such as a sharp source electrode to focus the field at the contact, and a blunt drain electrode to reduce the field there.

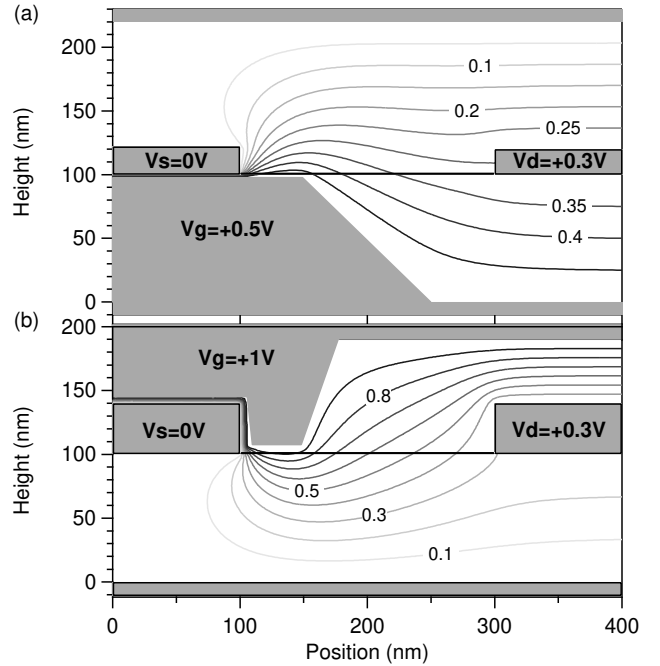


FIG. 1. Two possible geometries for an asymmetric device. Contour lines show the electrostatic potential. The applied voltages are given in the plot. (a) A bottom gate device with different oxide thicknesses at source (2 nm) and drain (100 nm) contact. The top plane is grounded. Adjacent contour lines differ by 0.05 V. (b) A local top gate close to the source contact. The bottom plane is grounded. Adjacent contour lines differ by 0.1 V.

To study the transport characteristics of these devices, we use a semiclassical model which has been described elsewhere^{2,4,7}. We assume ballistic transport within the NT (over the short distances of interest here)^{10,11}. For SB-CNFTs, the current is controlled by the rate of thermally assisted tunneling (at room temperature) through

the SBs at the source and drain contact. We neglect charge on the NT, which is a good approximation for the 0-state and in the turn-on regime^{2,8}.

For concreteness, we focus on the asymmetric bottom gate device, Fig. 1 (a). At the source contact the oxide thickness, t_{ox} , is only 2 nm. CNFETs with symmetric source and drain contacts of such low oxide thickness have been fabricated and show very good turn-on performance^{4,7}. We first treat ideally ambipolar devices, where the metal Fermi level falls in the middle of the NT bandgap at each contact. The NT band gap is taken to be 0.6 eV, corresponding to a diameter of 1.4 nm. Other cases are discussed below.

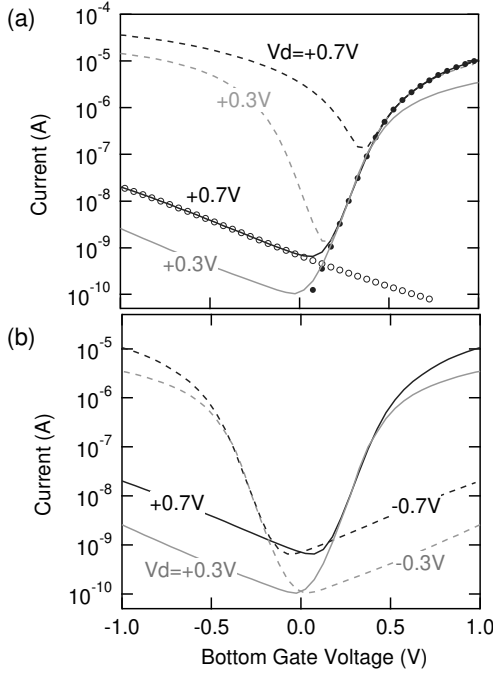


FIG. 2. (a) Calculated transfer characteristics for a symmetric ($t_{ox} = 2$ nm, dashed lines) and an asymmetric CNFET (geometry of Fig. 1 (a), solid lines). For the asymmetric CNFET, the electron and hole contributions to the current are given separately (filled and open circles, respectively) for $V_d = +0.7$ V. (b) Transfer characteristics of the asymmetric CNFET at positive V_d (solid lines) and negative V_d (dashed lines).

The calculated transfer characteristics for a symmetric CNFET with $t_{ox} = 2$ nm are shown as dashed lines in Fig. 2 (a). The quality of the turn-on performance can be quantified by the subthreshold slope, defined by $S = (d \log_{10} I / dV_g)^{-1}$, where I is the device current and V_g is the gate voltage. The value of S for the symmetric CNFET of Fig. 2 (a) is 110 mV/decade. (This is already within a factor of 2 of the thermal limit of a conventional transistor, 60 mV/decade.) However, the ratio between I_{on} - and I_{off} -current decreases with increased drain voltage V_d . At $V_d = +0.7$ V, the ratio is only two orders of magnitude, well below the range desired for transistors.

This drain voltage effect has been investigated in detail for such symmetric CNFETs^{7,8}, where it represents an important limitation.

In contrast, the asymmetric design of Fig. 1 (a) allows a high I_{on}/I_{off} ratio even at higher V_d , while preserving other good features of the behavior. This is shown by the solid lines in Fig. 2 (a). At positive V_d , the slope in the turn-on regime (e.g. $V_g = 0.3$) is the same as for the symmetric device. However, the I_{off} -current is much lower than for the symmetric device, and the I_{on}/I_{off} ratio is greatly improved, to over 4 orders of magnitude at $V_d = +0.7$ V.

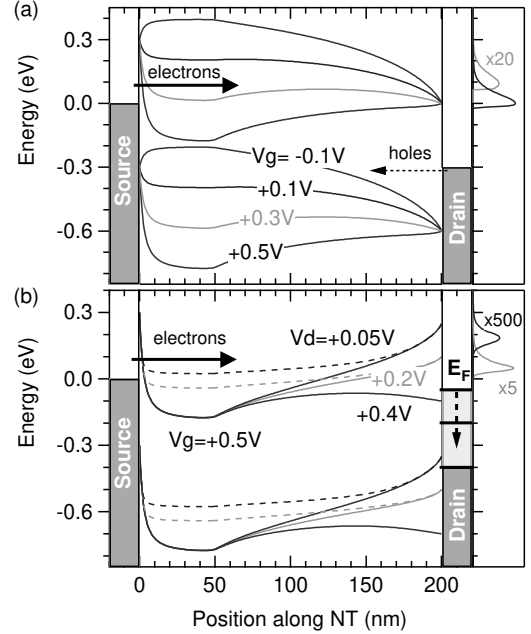


FIG. 3. The calculated band bending within the nanotube channel for the asymmetric device of Fig. 1 (a). (a) Fixed $V_d = +0.3$ V with varying V_g . The right side shows the contribution to the current vs. energy in arbitrary units for $V_g = +0.3$ V (gray line) and $+0.5$ V (black line). (b) Fixed $V_g = +0.5$ V with varying V_d . The right side shows the contribution to the current vs. energy in arbitrary units for $V_d = +0.05$ V (black line) and $+0.2$ V (gray line). Dashed lines illustrate (for $V_d = +0.05$ V and 0.2 V) the effect of including charge on the NT, within a local approximation². While the band bending is substantially different in the channel, the current in the subthreshold regime is virtually unchanged¹².

The contributions of electrons and holes to the current are shown separately for one case in Fig. 2 (a). For the asymmetric CNFET at positive V_d , the hole current is suppressed, changing the behavior from ambipolar for a symmetric device to n-type for the asymmetric device. By merely reversing the sign of V_d , one can instead suppress the electron current, making the same asymmetric CNFET behave as a p-type transistor with identical performance, as shown in Fig. 2 (b).

The transfer characteristics (I vs. V_g) of the asymmetric device can be understood based on the calculated band bending shown in Fig. 3(a) for $V_d = +0.3$ V. At large positive V_g ($+0.5$ V) the behavior is similar to a symmetric device — the SB at the source is sufficiently thin for electrons to be injected, and there is little or no barrier for them to be collected at the drain. Thus the current is relatively large [see Fig. 2(a)]. As V_g is reduced, the source SB becomes wider, until electron injection becomes negligible for $V_g = +0.1$ V.

For negative V_g , while the electron current remains negligible, holes can be injected at the drain and are then easily collected at the source. This is the origin of the ambipolar characteristic (and of the undesirable I_{on} -current) in symmetric devices⁷. In our asymmetric device, however, the geometry is chosen so that the SB at the drain remains rather wide, suppressing hole tunneling. Thus the device shows purely n-type character.

At negative V_d , the argument is reversed — electron transport is suppressed due to the barrier at the drain contact, while the hole current is as for a symmetric device. Thus by simply changing the sign of V_d , we can operate the same device as either an excellent p- or n-type transistor, with a turn-on performance controlled by the source contact geometry. This is a key advantage of the new device design. In principle, complementary n- and p-type transistors based on ohmic contacts (to the conduction and valence band respectively) would give even better performance; but the need for both kinds of contacts presents a formidable obstacle to such a design at present.

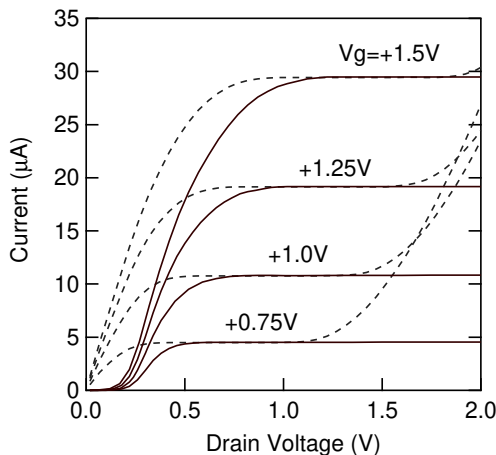


FIG. 4. Calculated output characteristics of the symmetric (dashed lines) and the asymmetric (solid lines) CNFET. Device geometries are the same as for Fig. 2.

The output characteristics (I vs. V_d) of the asymmetric and the symmetric CNFET are compared in Fig. 4. For the asymmetric device, the current starts to rise appreciable only for $V_d \geq$ half the NT bandgap. The lack of a linear regime of I vs. V_d for the asymmetric device does not hinder digital/logic applications which rely on the

plateau of saturating current. The plateaus are actually greatly improved for asymmetric CNFETs. For symmetric devices, these plateaus are limited by the onset of the drain leakage current⁷.

The output characteristics can be understood by examining the band bending at fixed V_g , Fig. 3(b). At $V_g = 0.5$ V, the SB at the source is sufficiently thin for high transmission. However, at low V_d ($= +0.05$ V) the electrons injected at the source contact cannot enter the drain contact due to the thick potential barrier¹². By increasing V_d the barrier at the drain contact is lowered and the injected electrons can be collected at the drain. Thus a V_d of about half the NT band gap is required for a significant flow of current (c.f. Fig. 4). With further increase of V_d the current saturates, being limited by the source or channel (both of which are controlled by V_g in the absence of short-channel effects) rather than by the drain.

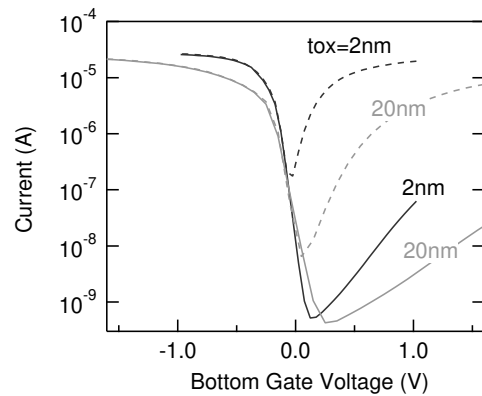


FIG. 5. Calculated transfer characteristics at $V_d = -0.2$ V for a NT with a bandgap of 0.3 eV and an ohmic contact to the valence band. Solid and dashed lines are for asymmetric and symmetric CNFET, respectively.

So far we have focused on ambipolar SB-CNFETs; but ohmic contacts could provide further performance improvements¹⁰. Ohmic contacts are most readily achieved for NTs having small bandgap¹⁰, in which case we find that drain leakage current is still an issue, except at very small V_d . Figure 5 shows calculations for a device having ohmic contacts to the valence band, and where the NT bandgap is 0.3 eV, as in Ref. 10. As expected, the sub-threshold slope is excellent (65 mV/dec for $t_{ox} = 2$ nm). However, for a symmetric CNFET, the SB to the conduction band (i.e. the bandgap) is only 0.3 eV. Thus positive V_g can induce substantial electron tunneling, leading to the behavior shown by dashed lines in Fig. 5. This electron tunneling is significant even for a 20 nm oxide; and for very thin oxides the effect is dramatic, as shown for $t_{ox} = 2$ nm.

For a CNFET having ohmic contacts, the leakage current can be suppressed by an asymmetric geometry, just as for the ambipolar devices described above. Thus, without excessively restricting V_d , one can achieve a dramatic

improvement of the On-Off ratio, suppressing the drain leakage current over a large range of V_g . As thin oxides are necessary for high performance CNFETs, the asymmetric device design may play a key role even for devices based on ohmic contacts, and even more so for Schottky barrier transistors.

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¹² The main effect of charge on the NT (which we neglect) is to alter the potential within the NT channel. Source and drain SBs are relatively unaffected in the energy range of significant tunneling current (c.f. Fig. 3). The current is limited by the channel only when there is negligible charge in the channel. As a result, the approximation gives a good description of the current (except perhaps in the fully "On" regime⁸), and so does not affect our conclusions.